CSE251: ELECTRONIC DEVICES AND CIRCUITS

EXPERIMENT 3:

STUDY OF IV CHARACTERISTICS OF DIODE AND ZENER DIODE

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SECTION: 12

GROUP: 03

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sk-03: Report

- Cover page [include course code, course title, name, student ID, group, semester, date of performance, date of submission]
- 2. Attach the signed Data Sheet.
- 3. Attach the graphs plotted using google sheets. Go to 'https://cutt.ly/l3QaTBf' to know how to plot in google sheet.
- 4. Add a brief Discussion at the end of the report.

Data Sheet

Diode IV Characteristics

8 = 0.488 KT

 $R=1k\Omega$ (measure the accurate resistance using the digital multi-meter)

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Supply Voltage, V_{DC} (v)	Diode Voltage, V_D (v)	Voltage across the Resistor, V_R (v)	Diode Current, $I_D = I_R = V_R/R$ (mA)
0	5.5×103 V	211 0.00	0.00
0.1	86.8×103V	0.00	0.00
0.2	VOIX F. 8FI	0.00	0.00
0.3	285.1×1034	0.00	0.00
0.4	369.9×10-34	0.00	0.00
0.5	0.438. V	81.6×103V	0.0822
0.6	0.476V	122.2 × 103 V	0.17.34
0.7	8.494V	VEOIX P.PFI	0.1821
0.8	0.509 V	243.3×103 V	0.2463
0.9	0.827V	361.1×103 V	0.3695
1	0.9341	0.420V	0.4251
2	0.593 V	1.358V	1.3748
4	0.639V	3.342V	3.3826
6	0.662 V	5.310 V	5.3748
8	0.677V	するスソ	7.4089
10	0.699 V	9.30 V	9,4129
12	VFP2.0	11.257	11.3866
13	0.701V	12.28 V	1214221
14	0.704V	13.254	13,4109

VT= 25X103

Calculation

Determining Ideality Factor, n

Let,
$$\alpha = \frac{1}{nV_T}$$

Take any two data from the table: $I_{D1} = I_S \exp(\alpha V_{D1})$ and $I_{D2} = I_S \exp(\alpha V_{D2})$

Taking ratio of I_{D1} and I_{D2} ,

$$\Rightarrow \frac{I_{D1}}{I_{D2}} = \exp(\alpha(V_{D1} - V_{D2}))$$

$$\Rightarrow \alpha = \frac{\ln(\frac{I_{D1}}{I_{D2}})}{V_{D1} - V_{D2}} = \frac{1}{aV_{T}} \qquad \Rightarrow n = \frac{1}{aV_{T}} = 1.92345$$

$$= 20.79587$$



Determining Static (R_D) and Dynamic (r_D) Resistance

$$R_D = V_D/I_D$$

$$r_D \approx \frac{nV_T}{I_D} =$$

Zener Diode IV Characteristics $R=470~\Omega~({\rm measure~the~accurate~resistance~using~the~digital~multi-meter})$

V	V_R	V_Z	$I_Z = V_R/R$
(volt)	(volt)	(volt)	(mA)
0	0	5 4X103	0
1	0	0'991	0
2	0	2.00	0
3	1.5×163	3.043	3.16 ×10.3
4	22X153	3.96	0.0468
4.9	172.9X103	172	0.3679
5	0.234	4.82	0.4939
5.1	0.265	4.86	0.5638
5.2	0'313	4.90	0,6659
5.3	0378	4.95	
5.4	0.406	THE REAL PROPERTY AND ADDRESS OF THE PERSON NAMED IN COLUMN TWO IS NOT THE PERSON NAMED IN COLUMN TWO IS NAMED IN COLUMN	086383
5.5	0.510		
6	0.827	5.12	1.7596
7	1.804	5.22	28383
8	2781	5'25	
9	378		80426
10	4.68		

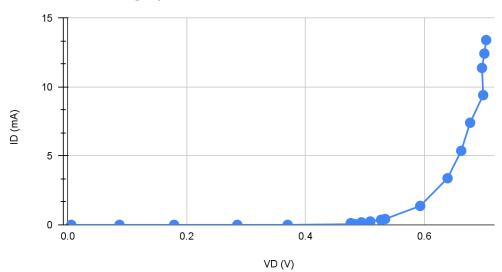
R=0470KD (4709



TASK 1:

А	В	С	D
V_DC (V)	VD (V)	VR (V)	ID (mA)
0	0.0055	0	0
0.1	0.0868	0	0
0.2	0.1787	0	0
0.3	0.2851	0	0
0.4	0.3699	0	0
0.5	0.483	0.0516	0.05222672065
0.6	0.476	0.1222	0.1236842105
0.7	0.494	0.1799	0.1820850202
0.8	0.509	0.2433	0.2462550607
0.9	0.527	0.3611	0.36548583
1	0.534	0.42	0.4251012146
2	0.593	1.358	1.374493927
4	0.639	3.342	3.382591093
6	0.662	5.31	5.374493927
8	0.677	7.32	7.408906883
10	0.699	9.3	9.412955466
12	0.697	11.25	11.38663968
13	0.701	12.28	12.4291498
14	0.704	13.25	13.41093117

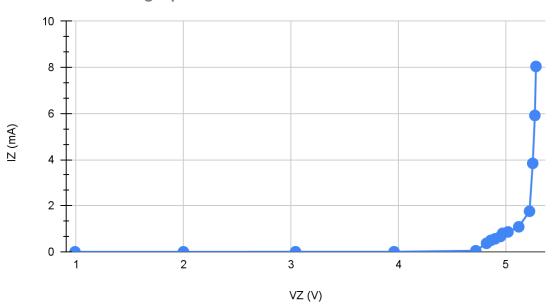
IV characteristic graph of diode



TASK 2:

Α	В	С	D
V (V)	VR (V)	VZ (V)	IZ (mA)
0	0	0.0054	0
1	0	0.991	0
2	0	2	0.003191489362
3	0.0015	3.043	0.003191489362
4	0.022	3.96	0.04680851064
4.9	0.1729	4.72	0.3678723404
5	0.234	4.82	0.4978723404
5.1	0.265	4.86	0.5638297872
5.2	0.313	4.9	0.6659574468
5.3	0.378	4.95	0.8042553191
5.4	0.406	4.97	0.8638297872
5.5	0.51	5.02	1.085106383
6	0.827	5.12	1.759574468
7	1.804	5.22	3.838297872
8	2.781	5.25	5.917021277
9	3.78	5.27	8.042553191
10	4.68	5.28	9.957446809

IV characteristic graph of zener diode



DISCUSSION

For Diode in task 1, the porande of diode is connected to the neglection and the cathode is connected to ground. Do nottage is applied according to the values as your in data sheet. For each supplied voltage, connesponding voltage across diode and negligible are measured using nultimeter. I

Ann Jennes Diode in task I, the eathode of genes diode is connected to the nesistor and the anode is connected to the agent the voltage across expand diode and nesiston using multimeter beward the break down and nesiston using multimeter beward the break down point of diode.

Google spreadsheets for task 1 and task 2 :

CSE251_LAB3